



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re application of

NANDAKUMAR

Serial No. 09/252,514 (TI-23103)

Filed February 18, 1999

For: DUAL-COUNTERDOPED CHANNEL FIELD EFFECT TRANSISTOR AND METHOD

Art Unit 2811

Examiner S. Crane

Commissioner for Patents
Washington, D. C. 20231

Sir:

AMENDMENT UNDER 37 C.F.R. 1.111

In response to the Office action dated June 5, 2001, please amend the above identified application as follows:

In the specification:

Amend the paragraph on page 6, lines 22 to 34 as follows:

"Referring to FIGURE 1E, source/drain regions 34 are formed around source/drain pockets 32 using ion implantation. In this example, source/drain [pockets 32] regions 34 are implanted with an n-type material such as arsenic.. Although source/drain pockets 32 are shown extending around and within source/drain region 34 and adjoining isolation trenches 20, it will be understood that source/drain pockets 32 may extend only along the inside portion of source/drain regions 34, the latter adjoining the channel region 24. Alternatively, a deeper